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implanted. Even if the photoresist stands erect at the smaller process technologies, the halo implant will not reach the targeted areas.--

#### IN THE ABSTRACT

D4

Please replace the Abstract with the following rewritten Abstract:

--A method and system for providing a halo implant to a semiconductor device is disclosed. The method and system includes providing a thin photoresist layer that covers a substantial amount of an active area including a source region and a drain region of the semiconductor device. The method and system further includes providing the halo implant to the semiconductor device, using the thin photoresist layer as a mask.

Utilizing this thin photoresist layer, taking into account other height variables, the source and drain regions can be opened only as needed. At a 45° angle, the implant can be delivered to all transistors in the circuit in the targeted area as well as getting only a large amount of the dose (up to  $\frac{3}{4}$  of the dose) to the transistor edge which sits on the trench edge.--

#### IN THE CLAIMS

Applicants note that claims 1 and 8 are not amended to overcome prior art but to more clearly claim the subject matter described in the specification. The amendments made to claims 1 and 8 are not narrowing in scope but instead are broader in scope and therefore no prosecution history estoppel arises from the amendments to claims 1 and 8. *Festo Corp v. Shoketsu Kinzoku Kogyo Kabushiki Co.*, 62 USPQ2d 1705, 1711-1712 (2002); 56 USPQ2d 1865, 1870 (Fed. Cir. 2000). Further, the amendments made to claims 1 and 8 were not made for a substantial reason related to patentability and therefore no prosecution history estoppel arises from such amendments. See *Festo Corp.*, 62 USPQ2d 1705 at 1707 (2002);